Analog Multiplexer / **Demultiplexer**

High-Performance Silicon-Gate CMOS

The MC74LVX8053 utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. This analog multiplexer/demultiplexer controls analog voltages that may vary across the complete power supply range (from V_{CC} to GND).

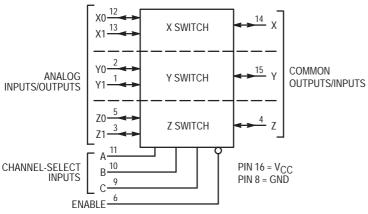
The LVX8053 is similar in pinout to the high–speed HC4053A, and the metal–gate MC14053B. The Channel–Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel-Select and Enable inputs are compatible with standard CMOS outputs; with pull-up resistors they are compatible with LSTTL outputs.

This device has been designed so that the ON resistance (R_{on}) is more linear over input voltage than R_{on} of metal-gate CMOS analog switches.

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range $(V_{CC} GND) = 2.0 \text{ to } 6.0 \text{ V}$
- Digital (Control) Power Supply Range (V_{CC} GND) = 2.0 to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate Counterparts
- Low Noise
- In Compliance With the Requirements of JEDEC Standard No. 7A
- Chip Complexity: LVX8053 156 FETs or 39 Equivalent Gates

LOGIC DIAGRAM Triple Single-Pole, Double-Position Plus Common Off



NOTE: This device allows independent control of each switch. Channel–Select Input A controls the X–Switch, Input B controls the Y–Switch and Input C controls the Z–Switch



ON Semiconductor

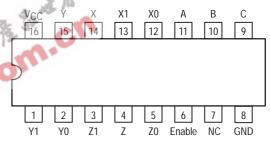
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16-LEAD SOIC D SUFFIX CASE 751B 16-LEAD TSSOP DT SUFFIX CASE 948F

PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 11 of this data sheet.

FUNCTION TABLE - MC74LVX8053

Control Inputs						
Select Enable C B A				ON	l Chann	els
L L L L	LLHH	L H H L	L H L H L	Z0 Z0 Z0 Z0 Z1 Z1	Y0 Y0 Y1 Y1 Y0 Y0	X0 X1 X0 X1 X0 X1
L L H	H H X	H H X	L H X	Z1 Z1 Z1	Y1 Y1 Y1 NONE	X0 X1

X = Don't Care

ORDERING INFORMATION

Device	Package	Shipping
MC74LVX8053D	SOIC	48 Units/Rail
MC74LVX8053DR2	SOIC	2500 Units/Reel
MC74LVX8053DT	TSSOP	96 Units/Rail
MC74LVX8053DTR2	TSSOP	2500 Units/Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	Positive DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
VIS	Analog Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V _{in}	Digital Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I	DC Current, Into or Out of Any Pin	± 20	mA
PD	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C

^{*}Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	Positive DC Supply Voltage (Referenced to GND)	2.0	6.0	V
VIS	Analog Input Voltage	0.0	VCC	V
V _{in}	Digital Input Voltage (Referenced to GND)	GND	Vcc	V
V _{IO} *	Static or Dynamic Voltage Across Switch	26	1.2	V
TA	Operating Temperature Range, All Package Types	- 55	+ 85	°C
t _r , t _f	Input Rise/Fall Time (Channel Select or Enable Inputs) $ \begin{array}{c} V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V} \end{array} $	0	100	ns/V
	$V_{CC} = 5.0 V \pm 0.5 V$	0	20	

^{*}For voltage drops across switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

[†]Derating — SOIC Package: - 7 mW/°C from 65° to 125°C

DC CHARACTERISTICS — Digital Section (Voltages Referenced to GND)

			VCC	Guaranteed Limit		nit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec	2.0 3.0 4.5 5.5	1.50 2.10 3.15 3.85	1.50 2.10 3.15 3.85	1.50 2.10 3.15 3.85	V
VIL	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec	2.0 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	V
l _{in}	Maximum Input Leakage Current, Channel–Select or Enable Inputs	V _{in} = V _{CC} or GND,	5.5	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and VIS = VCC or GND; VIO = 0 V	5.5	4	40	160	μΑ

DC ELECTRICAL CHARACTERISTICS Analog Section

				Gu	aranteed Lii	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}} \text{ to GND}$ $ I_{\text{S}} \le 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	40 30 25	45 32 28	50 37 30	Ω
		$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{IS}} = V_{\text{CC}} \text{ or GND (Endpoints)}$ $ I_{\text{S}} \leq 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	30 25 20	35 28 25	40 35 30	
ΔR _{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{IS}} = 1/2 (V_{\text{CC}} - \text{GND})$ $ I_{\text{S}} \le 10.0 \text{ mA}$	3.0 4.5 5.5	15 8.0 8.0	20 12 12	25 15 15	Ω
l _{off}	Maximum Off–Channel Leakage Current, Any One Channel	V _{in} = V _{IL} or V _{IH} ; V _{IO} = V _{CC} or GND; Switch Off (Figure 3)	5.5	0.1	0.5	1.0	μА
	Maximum Off–Channel Leakage Current, Common Channel	$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}};$ $V_{\text{IO}} = V_{\text{CC}} \text{ or GND};$ Switch Off (Figure 4)	5.5	0.1	1.0	2.0	
I _{on}	Maximum On–Channel Leakage Current, Channel–to–Channel	V _{in} = V _{IL} or V _{IH} ; Switch-to-Switch = V _{CC} or GND; (Figure 5)	5.5	0.1	1.0	2.0	μА

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 3 \text{ ns}$)

	Symbol Parameter		Gu			
Symbol			–55 to 25°C	≤85°C	≤125°C	Unit
^t PLH [,] ^t PHL	Maximum Propagation Delay, Channel–Select to Analog Output (Figure 9)	2.0 3.0 4.5 5.5	30 20 15 15	35 25 18 18	40 30 22 20	ns
^t PLH [,] ^t PHL	Maximum Propagation Delay, Analog Input to Analog Output (Figure 10)	2.0 3.0 4.5 5.5	4.0 3.0 1.0 1.0	6.0 5.0 2.0 2.0	8.0 6.0 2.0 2.0	ns
tPLZ, tPHZ	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	2.0 3.0 4.5 5.5	30 20 15 15	35 25 18 18	40 30 22 20	ns
^t PZL [,] ^t PZH	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	2.0 3.0 4.5 5.5	20 12 8.0 8.0	25 14 10 10	30 15 12 12	ns
C _{in}	Maximum Input Capacitance, Channel–Select or Enable Inputs		10	10	10	pF
C _{I/O}	Maximum Capacitance Analog I/O		35	35	35	pF
	(All Switches Off) Common O/I	- Oc 3	50	50	50	
	Feedthrough	13	1.0	1.0	1.0	

C _{PD}			Typical @ 25°C, V _{CC} = 5.0 V	pF
	Power Dissipation Capacitance (Figure 13)*		45	

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

			VCC	Limit*	
Symbol	Parameter	Condition	V	25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 6)	$ f_{in} = 1 \text{MHz Sine Wave; Adjust } f_{in} \text{ Voltage to Obtain } \\ 0 \text{dBm at V}_{OS}; \text{ Increase } f_{in} \text{ Frequency Until dB} \\ \text{Meter Reads } -3 \text{dB;} \\ \text{R}_L = 50 \Omega, C_L = 10 \text{pF} $	3.0 4.5 5.5	120 120 120	MHz
_	Off–Channel Feedthrough Isolation (Figure 7)	f_{in} = Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V _{IS} f_{in} = 10kHz, R _L = 600 Ω , C _L = 50pF	3.0 4.5 5.5	-50 -50 -50	dB
		f _{in} = 1.0MHz, R _L = 50Ω, C _L = 10pF	3.0 4.5 5.5	–37 –37 –37	
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 8)	$V_{in} \le 1 \text{MHz Square Wave (t}_{\Gamma} = \text{t}_{f} = 6 \text{ns); Adjust R}_{L}$ at Setup so that $I_{S} = 0 \text{A};$ Enable = GND $R_{L} = 600 \Omega, C_{L} = 50 \text{pF}$	3.0 4.5 5.5	25 105 135	mVpp
		$R_L = 10k\Omega$, $C_L = 10pF$	3.0 4.5 5.5	35 145 190	
_	Crosstalk Between Any Two Switches (Figure 12)	f_{in} = Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V _{IS} f_{in} = 10kHz, R_L = 600Ω , G_L = $50pF$	3.0 4.5 5.5	-50 -50 -50	dB
		f_{in} = 1.0MHz, R_L = 50 Ω , C_L = 10pF	3.0 4.5 5.5	-60 -60 -60	
THD	Total Harmonic Distortion (Figure 14)	$f_{in} = 1 \text{kHz}, \ R_L = 10 \text{k}\Omega, \ C_L = 50 \text{pF}$ $THD = THD_{measured} - THD_{source}$ $V_{IS} = 2.0 \text{Vpp sine wave}$ $V_{IS} = 4.0 \text{Vpp sine wave}$ $V_{IS} = 5.5 \text{Vpp sine wave}$	3.0 4.5 5.5	0.10 0.08 0.05	%

^{*}Limits not tested. Determined by design and verified by qualification.

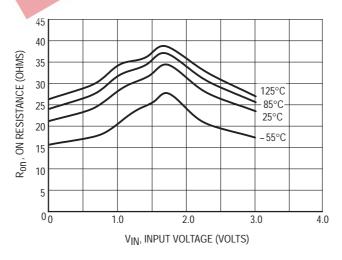
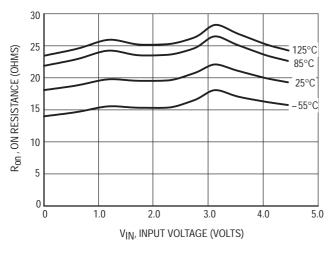


Figure 1a. Typical On Resistance, V_{CC} = 3.0 V



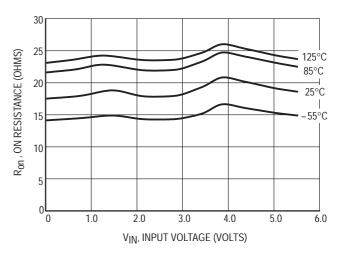


Figure 1b. Typical On Resistance, $V_{CC} = 4.5 \text{ V}$

Figure 1c. Typical On Resistance, $V_{CC} = 5.5 \text{ V}$

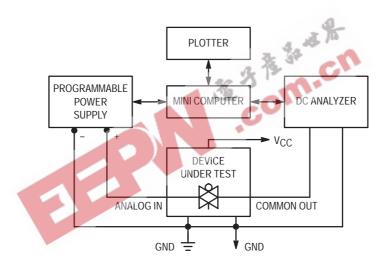


Figure 2. On Resistance Test Set-Up

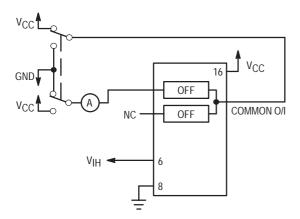


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

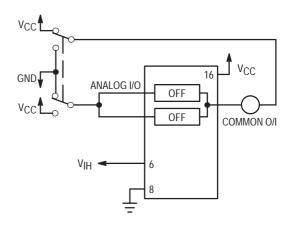


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

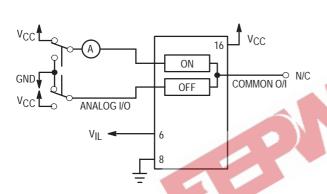


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

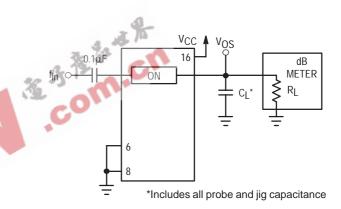


Figure 6. Maximum On Channel Bandwidth, Test Set-Up

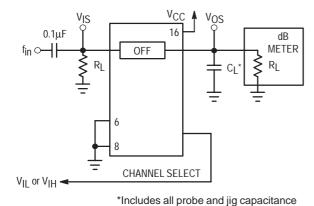
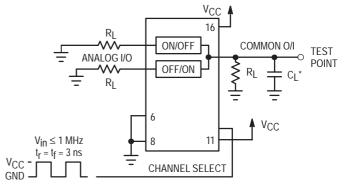
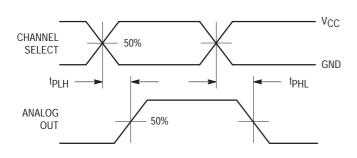


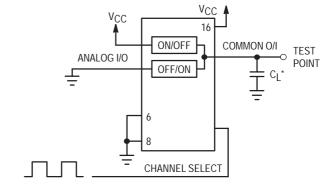
Figure 7. Off Channel Feedthrough Isolation, Test Set-Up



*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up





*Includes all probe and jig capacitance

Figure 9a. Propagation Delays, Channel Select to Analog Out

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

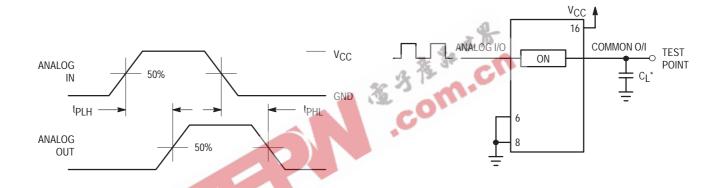


Figure 10a. Propagation Delays, Analog In to Analog Out

Figure 10b. Propagation Delay, Test Set-Up
Analog In to Analog Out

*Includes all probe and jig capacitance

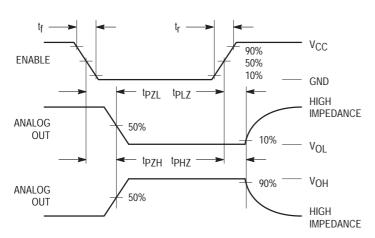


Figure 11a. Propagation Delays, Enable to Analog Out

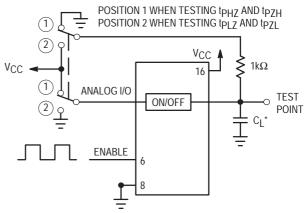
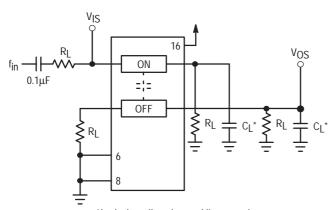


Figure 11b. Propagation Delay, Test Set-Up Enable to Analog Out



*Includes all probe and jig capacitance

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

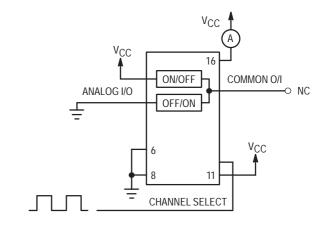


Figure 13. Power Dissipation Capacitance, Test Set-Up

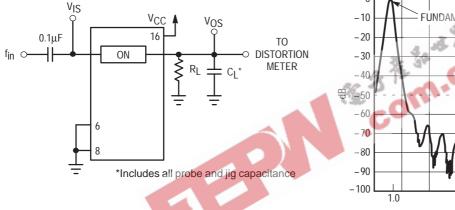


Figure 14a. Total Harmonic Distortion, Test Set-Up

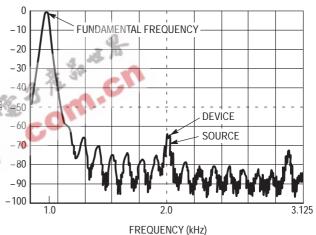


Figure 14b. Plot, Harmonic Distortion

APPLICATIONS INFORMATION

The Channel Select and Enable control pins should be at V_{CC} or GND logic levels. V_{CC} being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5V = logic high$$

 $GND = 0V = logic low$

The maximum analog voltage swing is determined by the supply voltages V_{CC} . The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below GND. In this example, the difference between V_{CC} and GND is five volts. Therefore, using the configuration of Figure 15, a maximum analog signal of five volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not

connected). However, tying unused analog inputs and outputs to V_{CC} or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$V_{CC} - GND = 2$$
 to 6 volts

When voltage transients above V_{CC} and/or below GND are anticipated on the analog channels, external Germanium or Schottky diodes (D_X) are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.

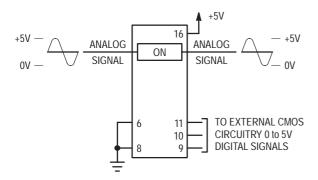


Figure 15. Application Example

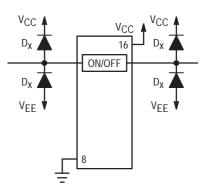


Figure 16. External Germanium or Schottky Clipping Diodes

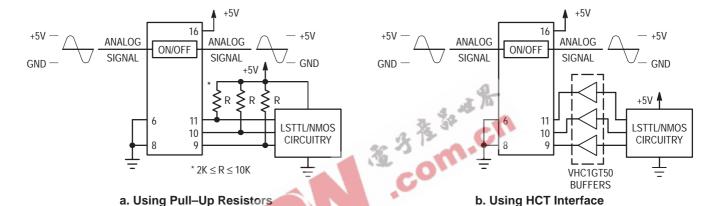


Figure 17. Interfacing LSTTL/NMOS to CMOS Inputs

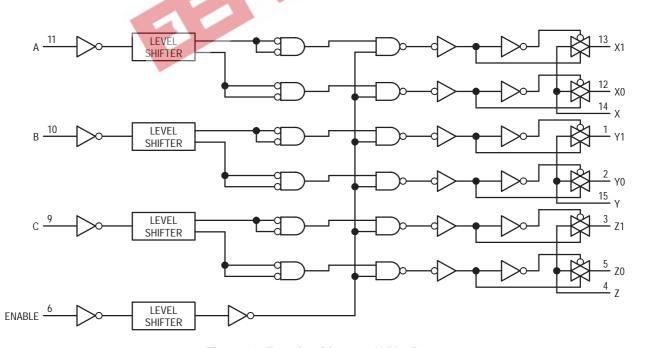
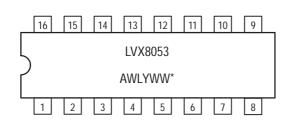
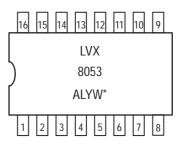


Figure 18. Function Diagram, LVX8053

MARKING DIAGRAMS

(Top View)





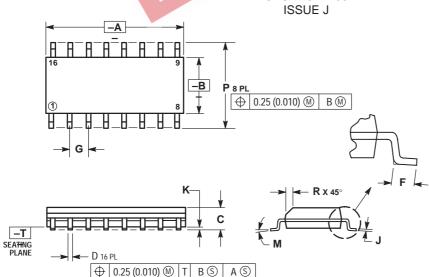
16-LEAD SOIC D SUFFIX **CASE 751B**

16-LEAD TSSOP **DT SUFFIX** CASE 948F

*See Applications Note #AND8004/D for date code and traceability information.

PACKAGE DIMENSIONS

D SUFFIX PLASTIC SOIC PACKAGE CASE 751B-05



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

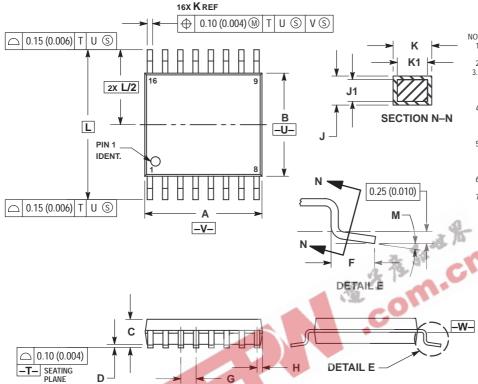
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.2	7 BSC	0.050) BSC
J	0.19	0.19 0.25		0.009
K	0.10	0.10 0.25		0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948F-01 **ISSUE O**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- . CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED
- PROTRUSION SHALL NOT EXCEED
 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION
 SHALL BE 0.08 (0.03) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 DIMENSION A AND B ARE TO BE DETERMINED AT
- DATUM PLANE -W-

	MILLIN	IETERS	INCHES				
DIM	MIN	MAX	MIN	MAX			
Α	4.90	5.10	0.193	0.200			
В	4.30	4.50	0.169	0.177			
С		1.20		0.047			
D	0.05	0.15	0.002	0.006			
F	0.50	0.75	0.020	0.030			
G	0.65	BSC	0.026 BSC				
Н	0.18	0.28	0.007	0.011			
J	0.09	0.20	0.004	0.008			
J1	0.09	0.16	0.004	0.006			
K	0.19	0.30	0.007	0.012			
K1	K1 0.19 0.2		0.007	0.010			
L	6.40 BSC		0.252 BSC				
M	0°	8°	0°	8°			

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